LV30200FCT

Rev.F Mar.-2016

DATA SHEET

/ Descriptions

TO-550F Ь ٦

Schottky Diode in a TO-220F Plastic Package.

/ Features

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Low forward voltage drop,low power losses,High efficiency operation.

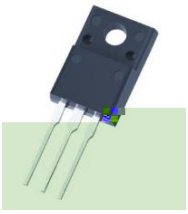
/ Applications

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For use in high frequency inverters, switching power supplies, freewheeling diodes,

OR-ing diode, dc-to-dc converters and reverse battery protection.

/ Equivalent Haq966 247 0 .(TD)ET0.70.82 0.45 rg57.54 45.54036.564 1806 ref62.4 44.02036.



PIN1 Anode PIN 2 Cathode PIN 3 Anode

/ h_{FE} Classifications & Marking

ŏ ب See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

Parameter	N Symbol	Rating	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RM} V_{RSM} V_{DC}	200	V
RMS Voltage	V_{RMS}	140	V
Average Rectified Forward Current	$I_{F(AV)}$	2×15	A
Non Repetitive Peak Surge Current	I_{FSM}	200	A
Thermal Resistance Junction to Case	$R_{\theta Jc}$	4.6	/W
Junction and Storage Temperature Range	T_j T_{stg}	-40 +150	

/ Electrical Characteristics(Ta=25)

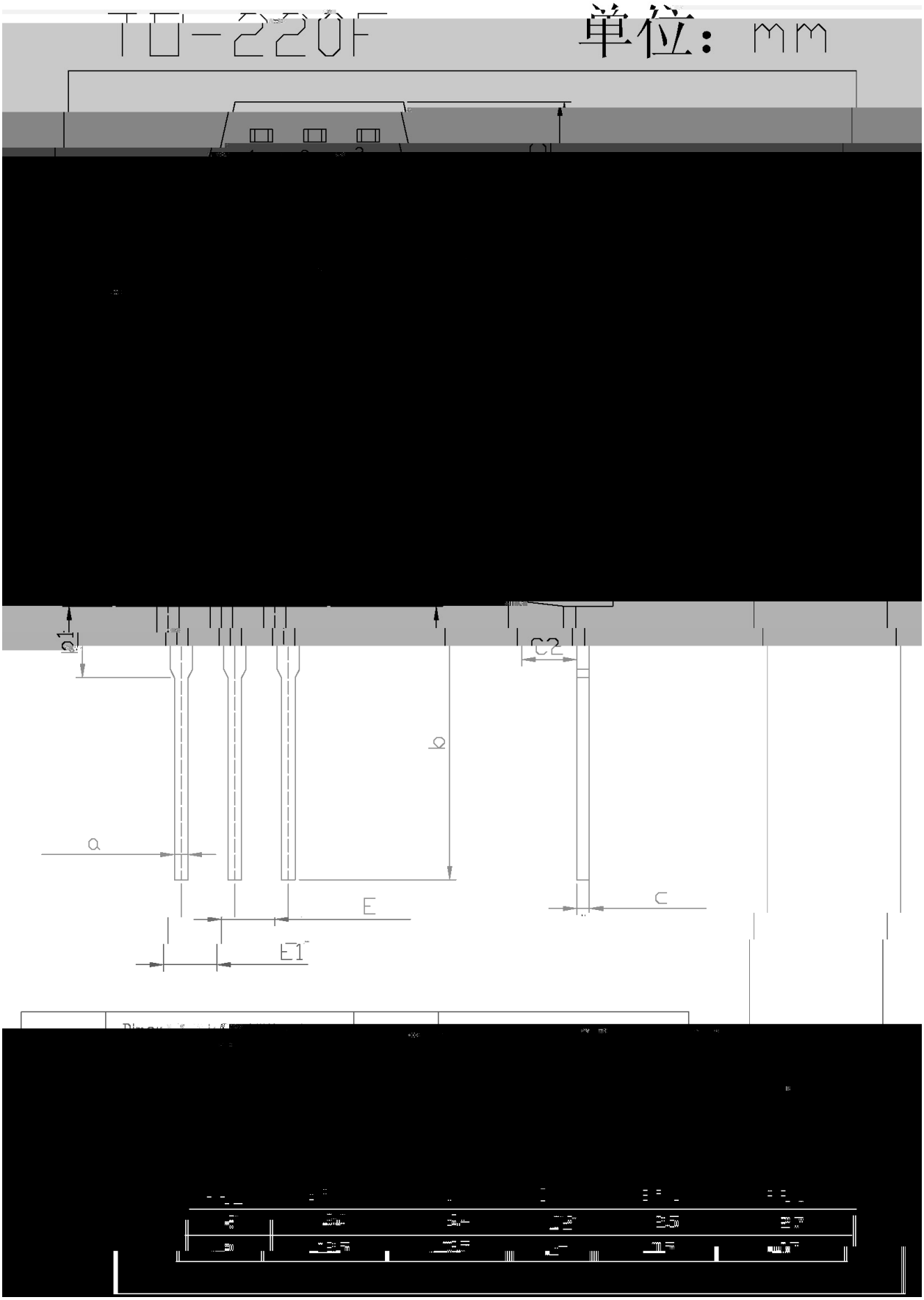
Parameter	N Symbol	Test Conditions	Min	Typ	Max	Unit
Breakdown Voltage	V_{BR}	I_R=1mA(Ta=25)	200			V
Forward Voltage	V_F	I_F =5A(Ta=25)		0.73	0.85	V
		I_F =10A(Ta=25)		0.80	0.95	V
		I_F =15A(Ta=25)		0.92	1.15	V
		I_F =5A(Ta=125)		0.58		V
		I_F =10A(Ta=125)		0.66		V
		I_F =15A(Ta=125)		0.71	0.85	V
Instantaneous Reverse Current	I_R Note 1	V_R=200V(Ta=25)		4	20	μA
		V_R=200V(Ta=125)		5	10	mA

/Notes

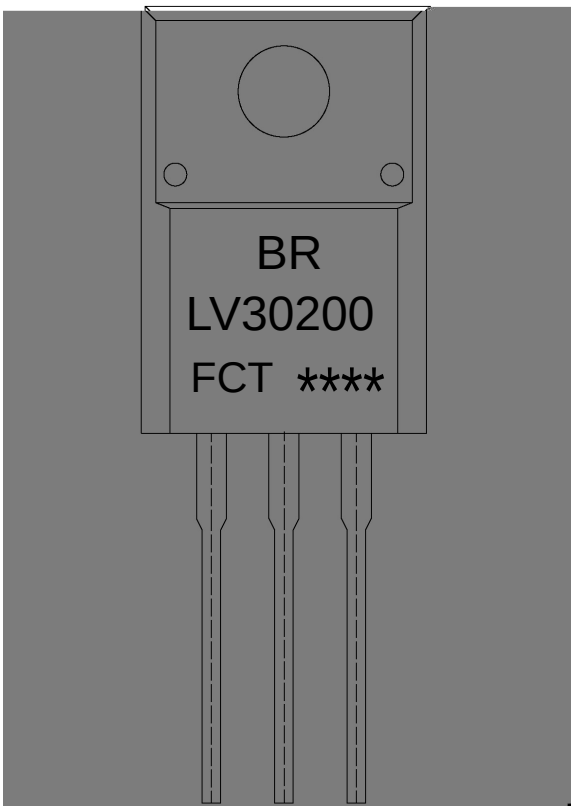
1. /Short duration pulse test used to minimize self-heating effect.

2. / Unless otherwise noted, values for the parameters of a single chip

/ Package



/ Marking Instructions



ER	
LV60500	
F:	
FT:	
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Note:

BR:	Company Code
LV60500	Product Type.
F:	Package Code
FT:	Internal Structure
****:	Lot No. Code, code change with Lot No.

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